

9/3/03

SHEET 1 OF 1

<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449	<b>26615</b> <small>PATENT TRADEMARK OFFICE</small>	ATTORNEY'S DKT No. H1505	APPLICATION No. Unassigned	
		APPLICANT(S) Bin YU et al.		
		FILING DATE September 3, 2003	GROUP Unassigned	

  

U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

  

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

  

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
<i>See</i>	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.
<i>See</i>	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.
	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.
	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.
<i>See</i>	Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.

  

EXAMINER <i>Debra Kuyper</i>	DATE CONSIDERED <i>8/30/05</i>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).